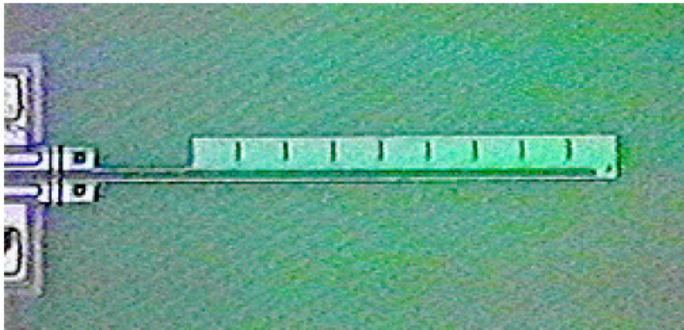


Thermal Actuator Simulation
EE686 – MEMS Evaluation
Spring 2006
Ivan Puchades

Polysilicon thermal actuator

MEMS – Actuators

POLYCRYSTALLINE SILICON THERMAL ACTUATORS



No current flow



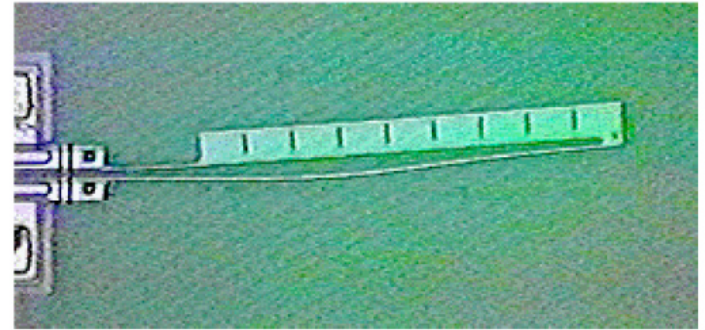
Rochester Institute of Technology
Microelectronic Engineering

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MEMS – Actuators

POLYCRYSTALLINE SILICON THERMAL ACTUATORS



Current flow



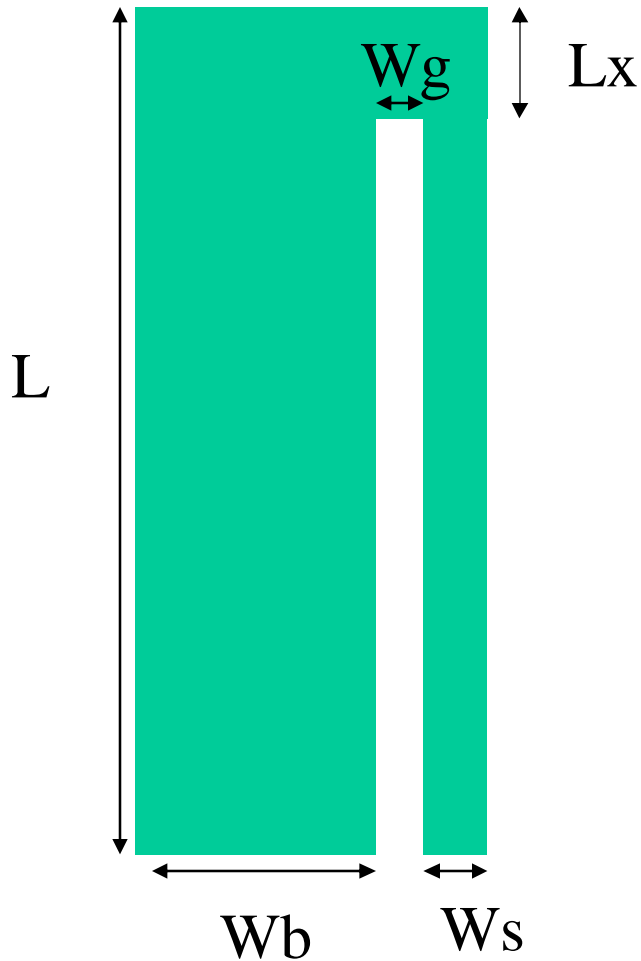
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Kevin Munger

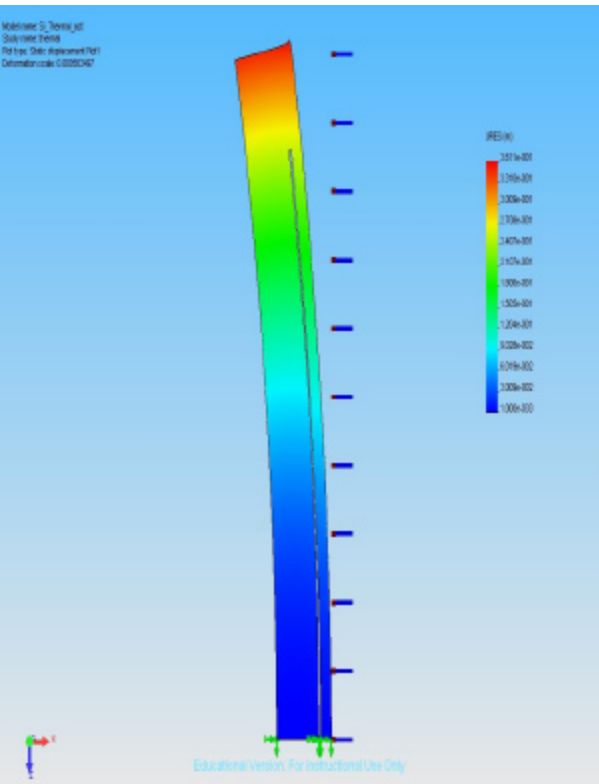
SolidWorks Simulation Dimensions



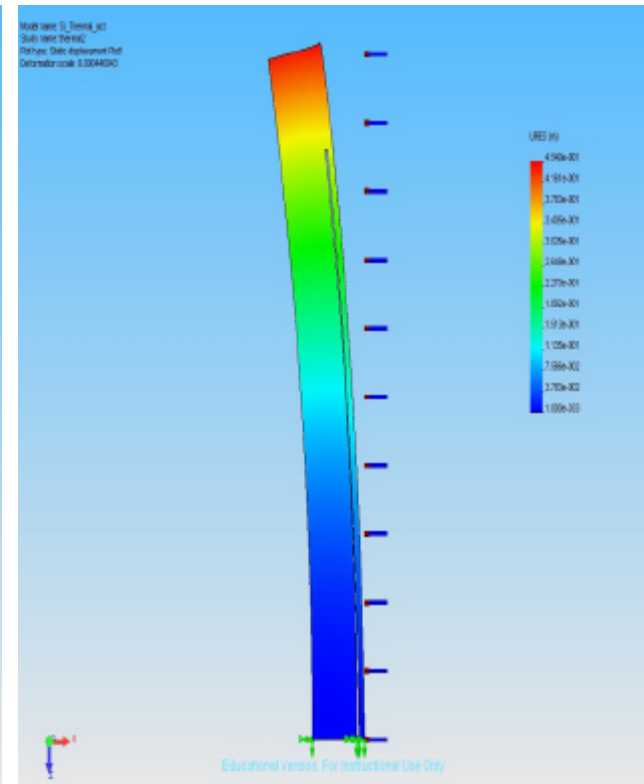
	L	Wb	Wg	Ws	Lx
1	2mm	200 μ m	10 μ m	50 μ m	300 μ m
2	2mm	200 μ m	10 μ m	25 μ m	300 μ m
3	2mm	200 μ m	10 μ m	10 μ m	300 μ m
4	2mm	200 μ m	10 μ m	25 μ m	200 μ m
5	2mm	200 μ m	10 μ m	25 μ m	100 μ m
6	2mm	200 μ m	10 μ m	25 μ m	10 μ m
7	2mm	200 μ m	100 μ m	25 μ m	300 μ m

All simulations performed with small arm at 400C

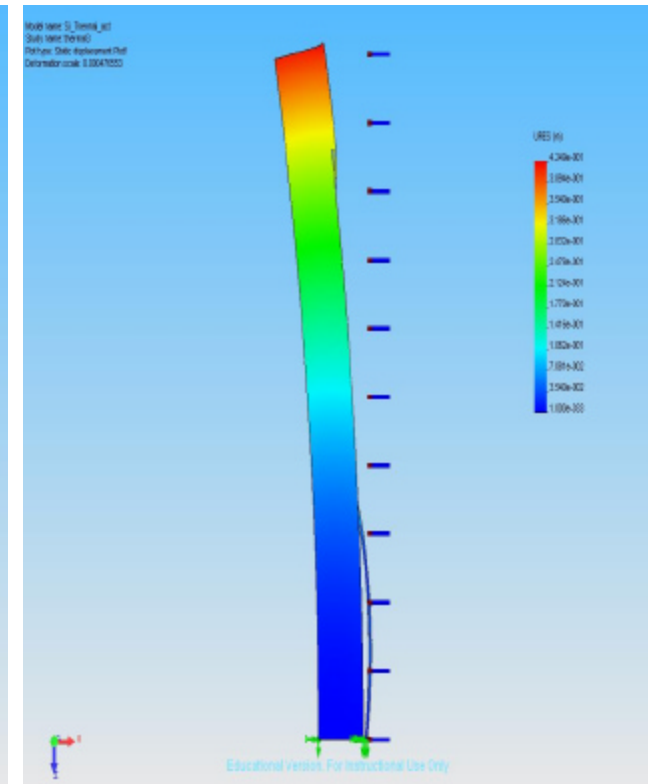
Varying small-arm width



10_50

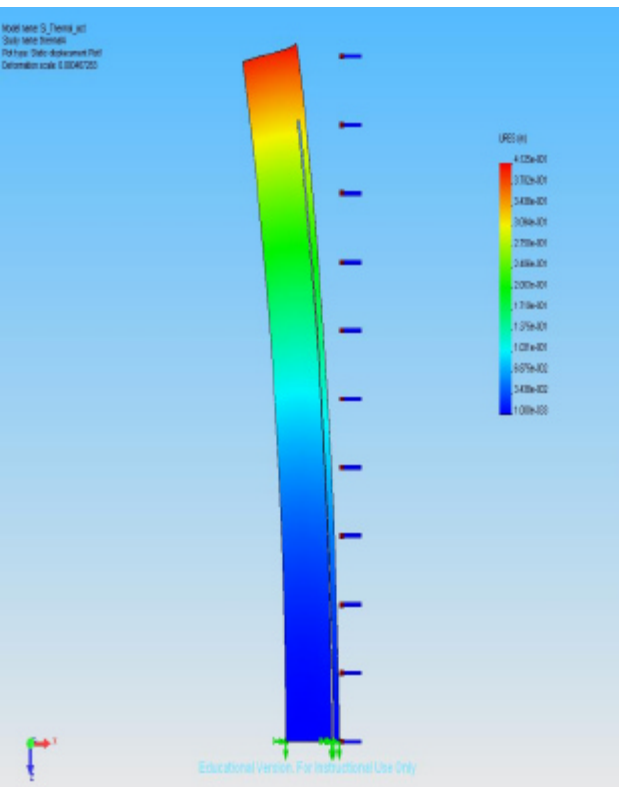


10_25

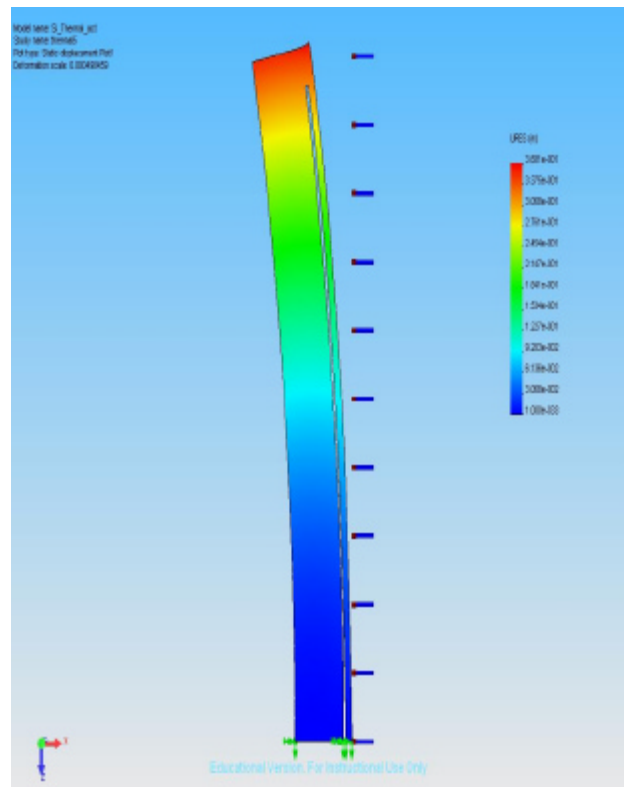


10_10

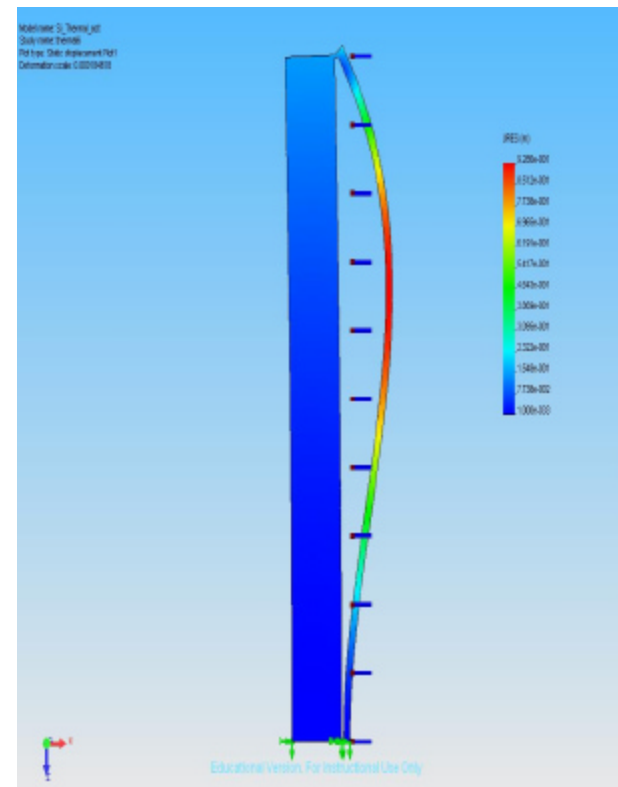
Varying Connection Width Lx



10_25_200

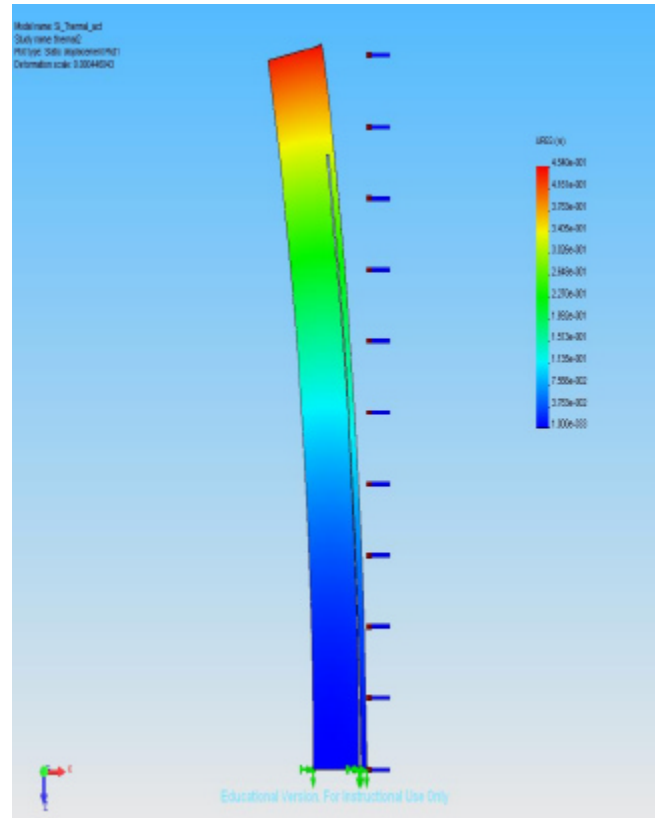
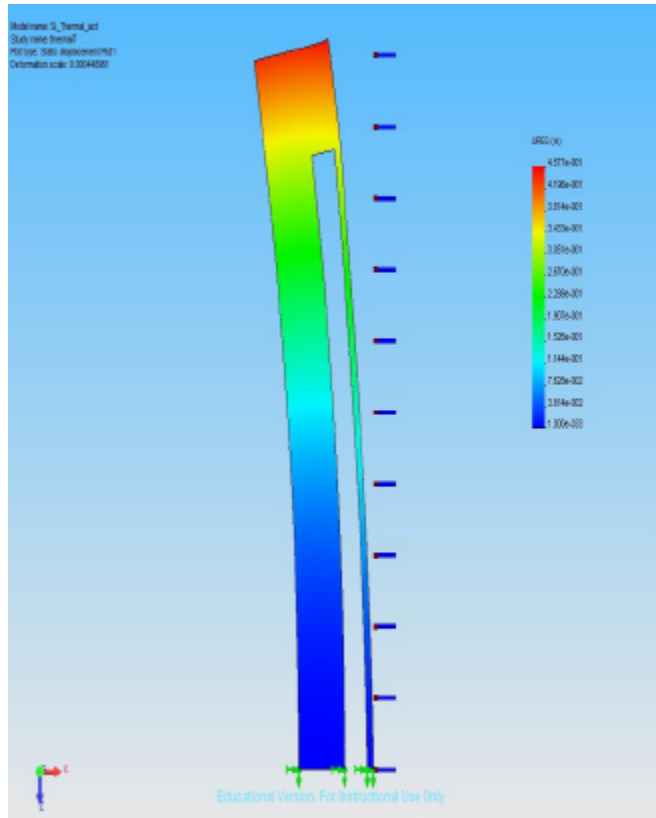


10_25_100



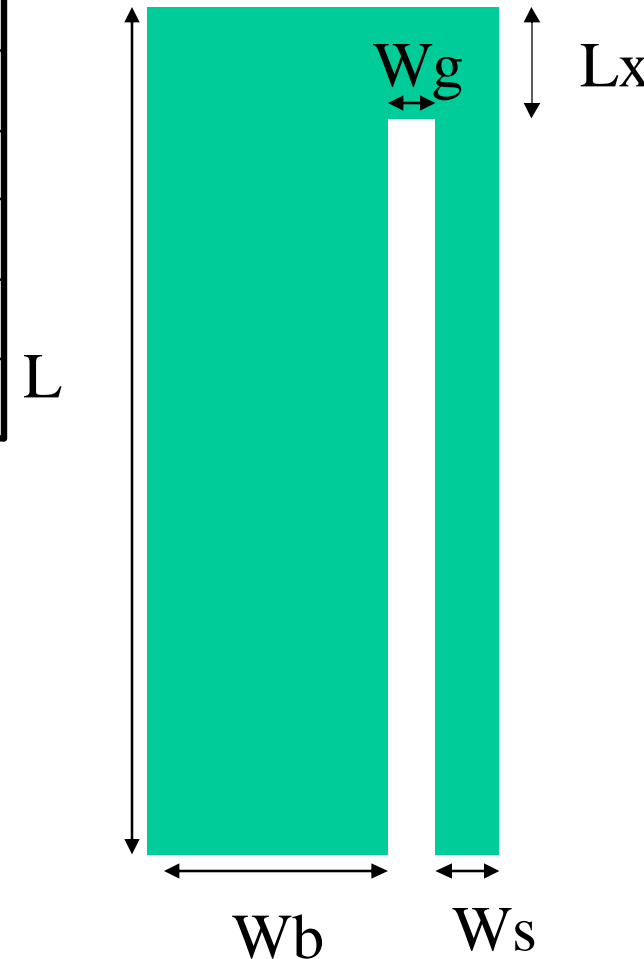
10_10_10

Increasing gap width



Summary

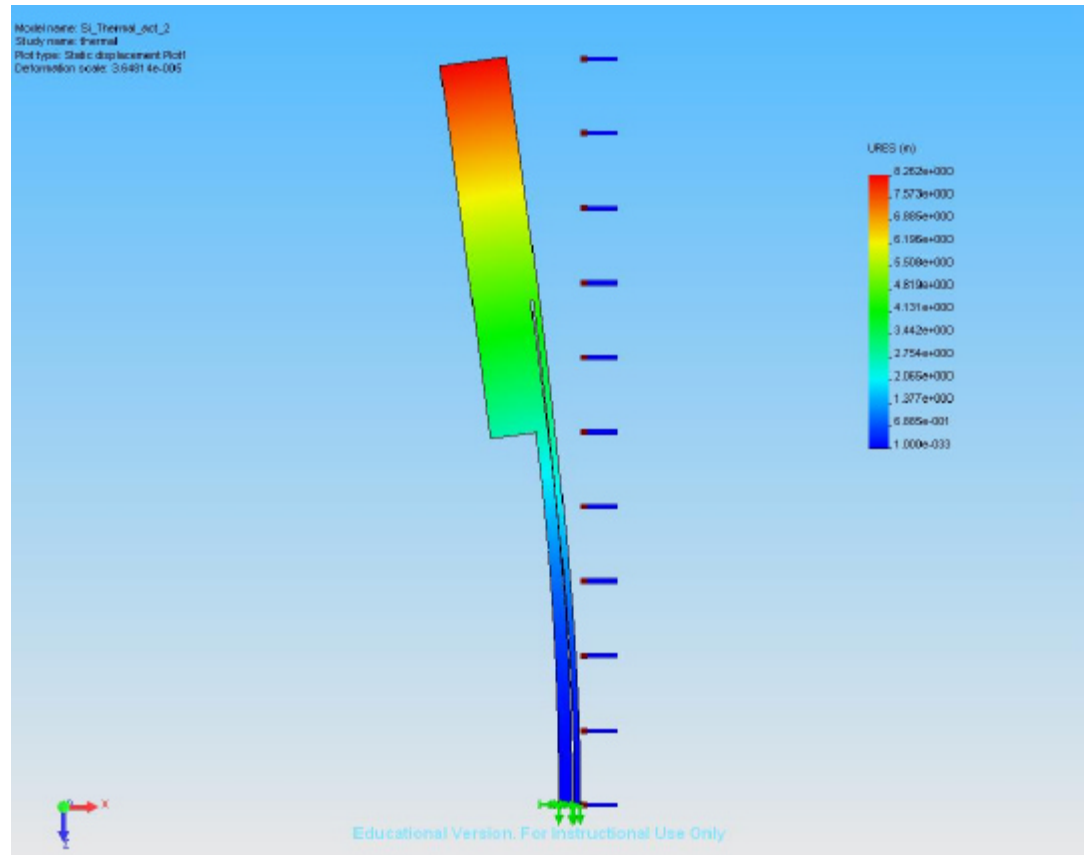
	L	W _b	W _g	W _s	L _x	Max. Disp.	Scale	Microns
1	2mm	200μm	10μm	50μm	300μm	3.611e-1	0.000563	203.3
2	2mm	200μm	10μm	25μm	300μm	4.54e-1	0.000446	202.5
3	2mm	200μm	10μm	10μm	300μm	-	-	
4	2mm	200μm	10μm	25μm	200μm	4.125e-1	0.000467	192.7
5	2mm	200μm	10μm	25μm	100μm	3.681e-1	0.000498	183.3
6	2mm	200μm	10μm	25μm	10μm	-	-	
7	2mm	200μm	100μm	25μm	300μm	4.577e-1	0.000448	205.1



To obtain max. displacements L_x has to be maintained at 300μm. W_g does not affect the max. displacement much but needs to be $>10\mu\text{m}$ to maintain structure integrity. Max. displacement of 300μm obtained in next page.

Future Work

- Simulate structure that resembles the real design better (max displacement increases to $301\mu\text{m}$ vs. the $205\mu\text{m}$ of previous structure)
- Vary parameters and apply DOE techniques to investigate optimal parameters for max displacement.



$W_s=25\mu\text{m}$, $L_x=300\mu\text{m}$, $W_g=10\mu\text{m}$
Max displacement= $301.4\mu\text{m}$